

MORRISON | FOERSTER

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Suggested Amendments

31. (Currently Amended) A method for creating an epitaxial layer on a nitride monocrystal, comprising:

obtaining a bulk nitride monocrystal by a process according to claim 1;

contacting ammonia with a mineralizer comprising a Group I azide in a pressurized reaction vessel to form a supercritical ammonia-containing solution comprising an ion of a Group I element;

dissolving a gallium-containing feedstock at a dissolution temperature and pressure condition under which the gallium feedstock dissolves in the supercritical ammonia-containing solution;

crystallizing a gallium-containing nitride on a surface of a seed at a crystallization temperature and pressure condition to obtain a nitride monocrystal,

wherein the crystallization temperature and pressure condition is determined using a temperature coefficient of solubility and a pressure coefficient of solubility of the gallium-containing nitride to be crystallized; and

growing an epitaxial layer on the nitride monocrystal.

34. (Canceled)

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